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Applicant(s) Khan et al.	
Filing Date September 27, 2001	Group Art Unit 2814

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LP	"Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.
	"Piezoeffect and Gate Current in AlGaN/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.
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